

**RADIATION HARDENED
POWER MOSFET
THRU-HOLE (Low-Ohmic TO-257AA)**
30V, P-CHANNEL
REF: MIL-PRF-19500/732
 **R5 TECHNOLOGY**
Product Summary

Part Number	Radiation Level	RDS(on)	I _D	QPL Part Number
IRHYS597Z30CM	100 kRads(Si)	0.072Ω	-20A*	JANSR2N7519T3
IRHYS593Z30CM	300 kRads(Si)	0.072Ω	-20A*	JANSF2N7519T3


Description

IR HiRel R5 technology provides high performance power MOSFETs for space applications. These devices have been characterized for both Total Dose and Single Event Effect (SEE) with useful performance up to LET of 80 (MeV/(mg/cm²)). The combination of low RDS(on) and low gate charge reduces the power losses in switching applications such as DC-DC converters and motor controllers. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching and temperature stability of electrical parameters.

Features

- Single Event Effect (SEE) Hardened
- Fast Switching
- Low RDS(on)
- Low Total Gate Charge
- Simple Drive Requirements
- Hermetically Sealed
- Electrically Isolated
- Ceramic Eyelets
- Light Weight
- ESD Rating: Class 1C per MIL-STD-750, Method 1020

Absolute Maximum Ratings
Pre-Irradiation

Symbol	Parameter	Value	Units
I _{D1} @ V _{GS} = -12V, T _C = 25°C	Continuous Drain Current	-20*	A
I _{D2} @ V _{GS} = -12V, T _C = 100°C	Continuous Drain Current	-18	
I _{DM} @ T _C = 25°C	Pulsed Drain Current ①	-80	
P _D @ T _C = 25°C	Maximum Power Dissipation	75	W
	Linear Derating Factor	0.6	W/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
E _{AS}	Single Pulse Avalanche Energy ②	200	mJ
I _{AR}	Avalanche Current ①	-20	A
E _{AR}	Repetitive Avalanche Energy ①	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-1.84	V/ns
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Lead Temperature	300 (0.063 in./1.6 mm from case for 10s)	
	Weight	4.3 (Typical)	

*Current is limited by package

For Footnotes refer to the page 2.

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	-30	—	—	V	V _{GS} = 0V, I _D = -1.0mA
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	-0.066	—	V/°C	Reference to 25°C, I _D = -1.0mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.072	Ω	V _{GS} = -12V, I _{D2} = -18A ④
V _{GS(th)}	Gate Threshold Voltage	-2.0	—	-4.0	V	V _{DS} = V _{GS} , I _D = -1.0mA
G _{fs}	Forward Transconductance	12	—	—	S	V _{DS} = -15V, I _{D2} = -18A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	-10	μA	V _{DS} = -24V, V _{GS} = 0V
		—	—	-25		V _{DS} = -24V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	V _{GS} = -20V
	Gate-to-Source Leakage Reverse	—	—	100		V _{GS} = 20V
Q _G	Total Gate Charge	—	—	45	nC	I _{D1} = -20A
Q _{GS}	Gate-to-Source Charge	—	—	20		V _{DS} = -15V
Q _{GD}	Gate-to-Drain ('Miller') Charge	—	—	13		V _{GS} = -12V
t _{d(on)}	Turn-On Delay Time	—	—	25	ns	V _{DD} = -15V
t _r	Rise Time	—	—	100		I _{D1} = -20A
t _{d(off)}	Turn-Off Delay Time	—	—	50		R _G = 7.5Ω
t _f	Fall Time	—	—	70		V _{GS} = -12V
L _S + L _D	Total Inductance	—	6.8	—	nH	Measured from Drain lead (6mm / 0.25 in from package) to Source lead (6mm / 0.25 in from package) with Source wire internally bonded from Source pin to Drain pad
C _{iss}	Input Capacitance	—	1590	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	934	—		V _{DS} = -25V
C _{rss}	Reverse Transfer Capacitance	—	114	—		f = 1.0MHz
R _G	Internal Gate Resistance	—	6.5	—		f = 1.0MHz, open drain

Source-Drain Diode Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-20*	A	
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	-80		
V _{SD}	Diode Forward Voltage	—	—	-5.0	V	T _J = 25°C, I _S = -20A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	—	75	ns	T _J = 25°C, I _F = -20A, V _{DD} ≤ -25V
Q _{rr}	Reverse Recovery Charge	—	—	125	nC	di/dt = -100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S + L _D)				

* Current is limited by package

Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	—	1.67	°C/W
R _{θJA}	Junction-to-Ambient (Typical Socket Mount)	—	—	80	

Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② V_{DD} = -25V, starting T_J = 25°C, L = 1.0mH, Peak I_L = -20A, V_{GS} = -12V
- ③ I_{SD} ≤ -20A, di/dt ≤ -180A/μs, V_{DD} ≤ -30V, T_J ≤ 150°C
- ④ Pulse width ≤ 300 μs; Duty Cycle ≤ 2%
- ⑤ Total Dose Irradiation with V_{GS} Bias. -12 volt V_{GS} applied and V_{DS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.
- ⑥ Total Dose Irradiation with V_{DS} Bias. -24 volt V_{DS} applied and V_{GS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

Radiation Characteristics

IR HiRel radiation hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at IR HiRel is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

Symbol	Parameter	100 kRads (Si) ¹		300 kRads (Si) ²		Units	Test Conditions
		Min.	Max.	Min.	Max.		
BV _{DSS}	Drain-to-Source Breakdown Voltage	-30	—	-30	—	V	V _{GS} = 0V, I _D = -1.0mA
V _{GS(th)}	Gate Threshold Voltage	-2.0	-4.0	-2.0	-5.0	V	V _{DS} = V _{GS} , I _D = -1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	-100	—	-100	nA	V _{GS} = -20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	100	—	100	nA	V _{GS} = 20V
I _{DSS}	Zero Gate Voltage Drain Current	—	-10	—	-10	μA	V _{DS} = -24V, V _{GS} = 0V
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (TO-3)	—	0.072	—	0.072	Ω	V _{GS} = -12V, I _{D2} = -18A
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (TO-257AA)	—	0.072	—	0.072	Ω	V _{GS} = -12V, I _{D2} = -18A
V _{SD}	Diode Forward Voltage ④	—	-5.0	—	-5.0	V	V _{GS} = 0V, I _S = -20A

1. Part numbers IRHYS597Z30CM (JANSR2N7519T3)

2. Part numbers IRHYS593Z30CM (JANSF2N7519T3)

IR HiRel radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Typical Single Event Effect Safe Operating Area

LET (MeV/(mg/cm ²))	Energy (MeV)	Range (μm)	VDS (V)				
			@VGS=0V	@VGS=5V	@VGS=10V	@VGS=15V	@VGS=20V
38 ± 5%	300 ± 7.5%	38 ± 7.5%	-30	-30	-30	-30	-30
62 ± 5%	355 ± 7.5%	33 ± 7.5%	-30	-30	-30	-30	-25
85 ± 5%	380 ± 7.5%	29 ± 7.5%	-30	-30	-30	-25	—

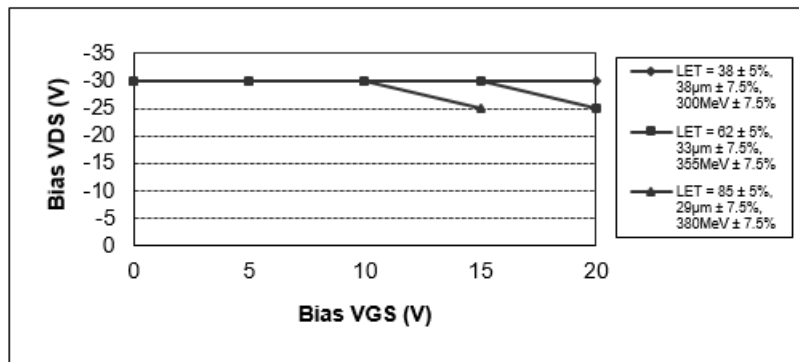


Fig a. Typical Single Event Effect, Safe Operating Area

For Footnotes, refer to the page 2.

Pre-Irradiation

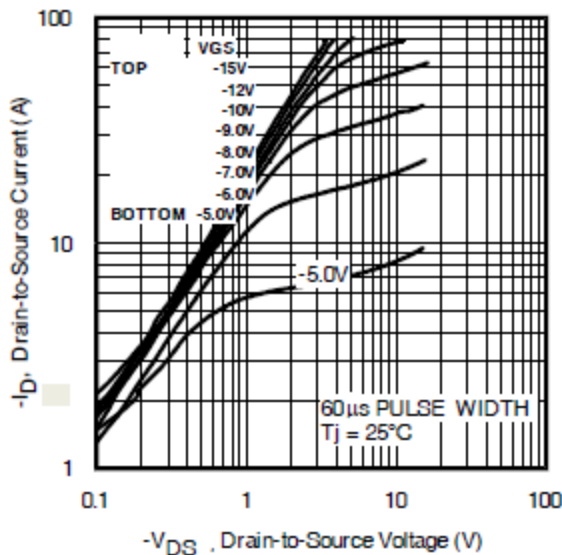


Fig 1. Typical Output Characteristics

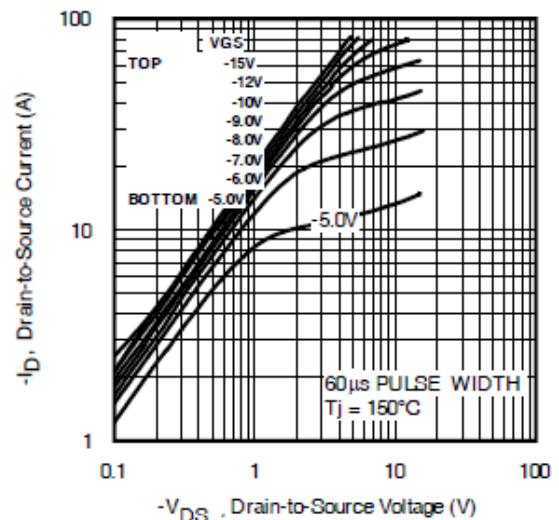


Fig 2. Typical Output Characteristics

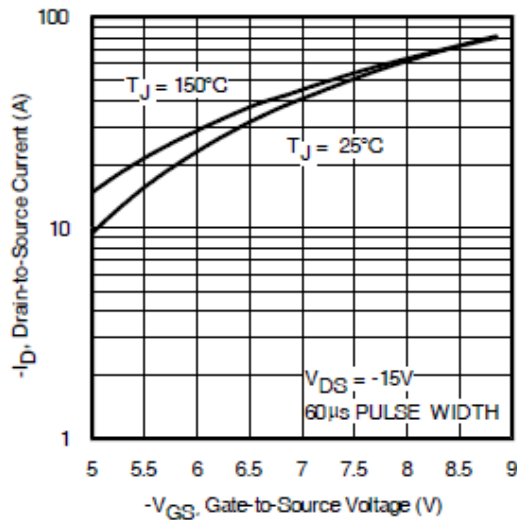


Fig 3. Typical Transfer Characteristics

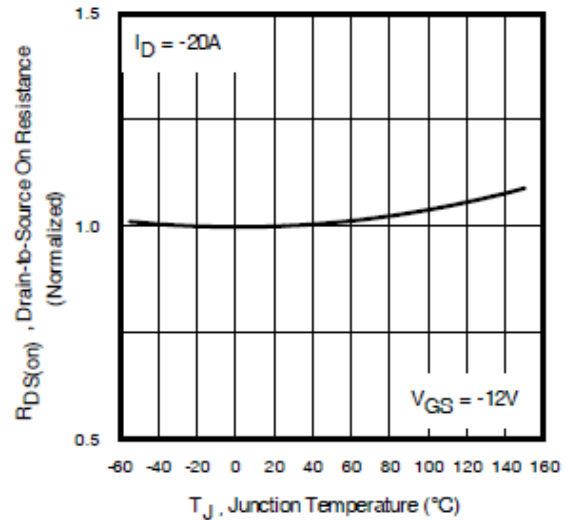


Fig 4. Normalized On-Resistance Vs. Temperature

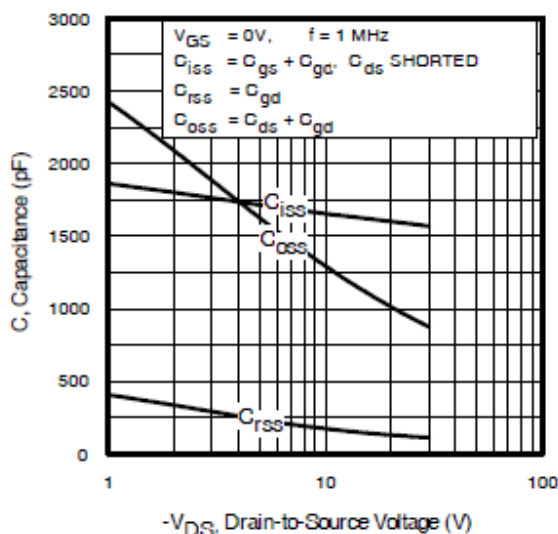


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

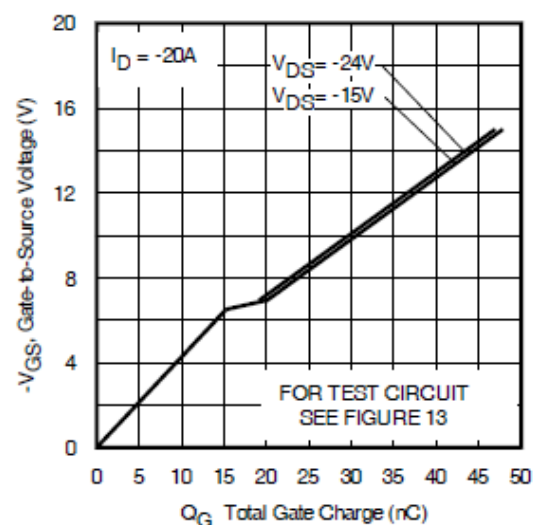


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

Pre-Irradiation

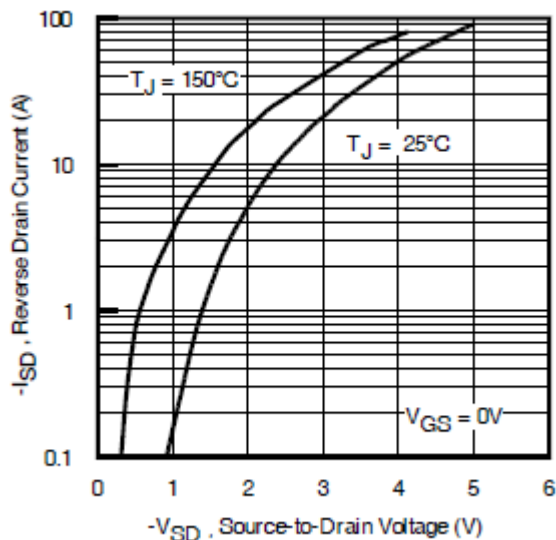


Fig 7. Typical Source-Drain Diode Forward Voltage

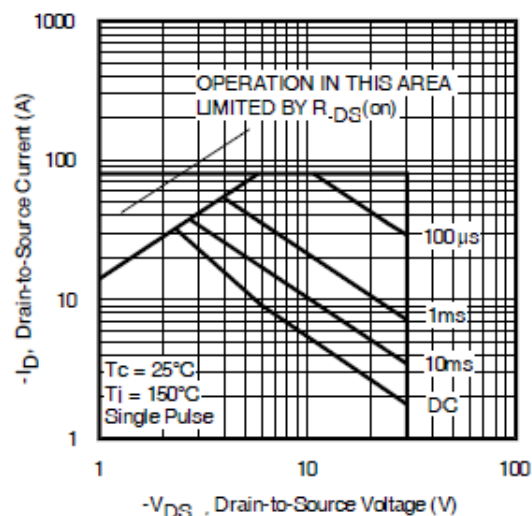


Fig 8. Maximum Safe Operating Area

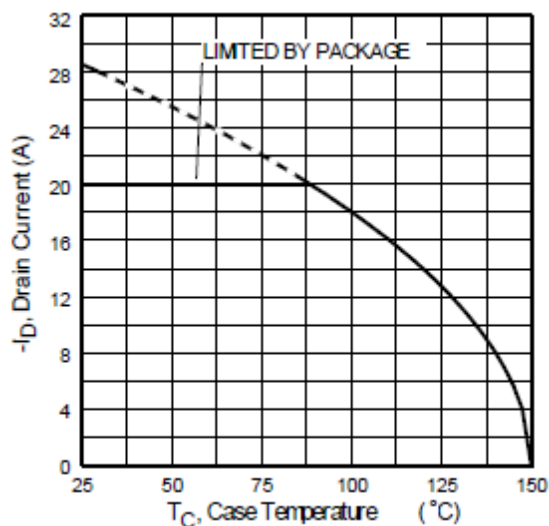


Fig 9. Maximum Drain Current Vs. Case Temperature

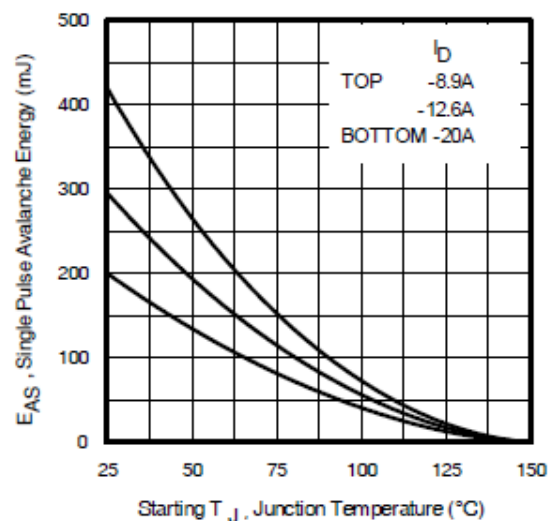


Fig 10. Maximum Avalanche Energy

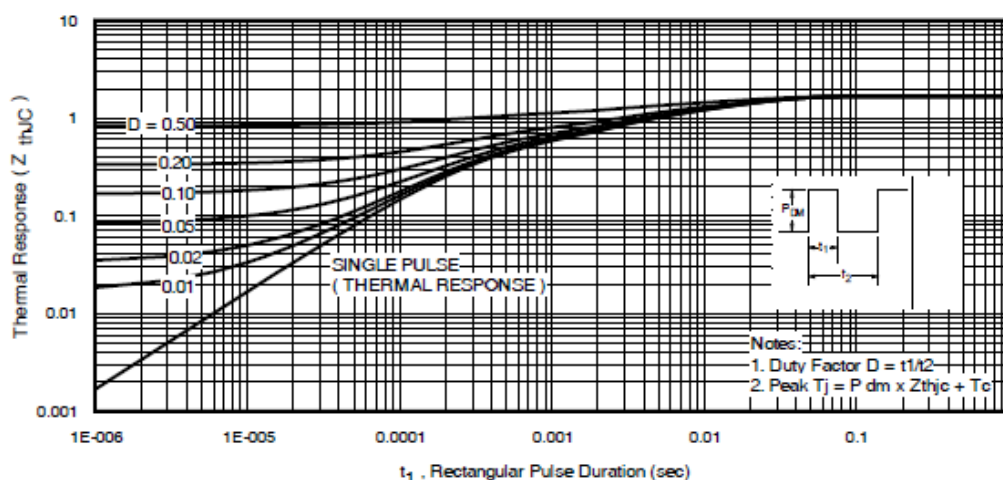


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Pre-Irradiation

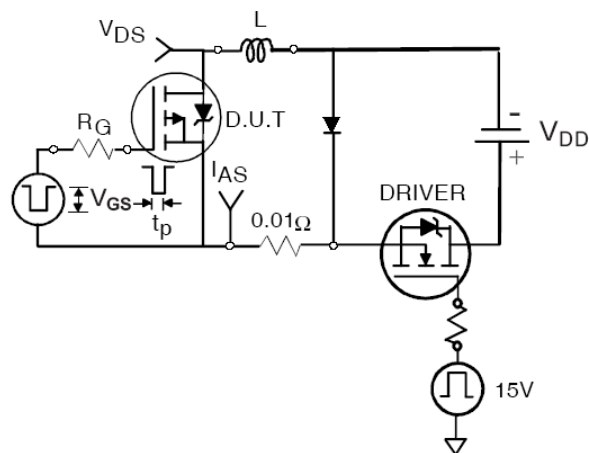


Fig 12a. Unclamped Inductive Test Circuit

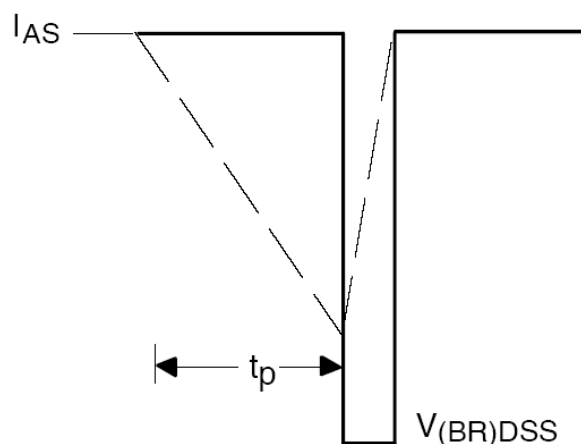


Fig 12b. Unclamped Inductive Wave-

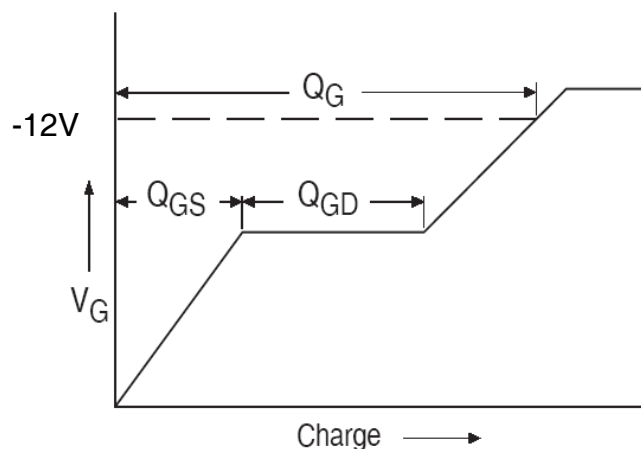


Fig 13a. Basic Gate Charge Waveform

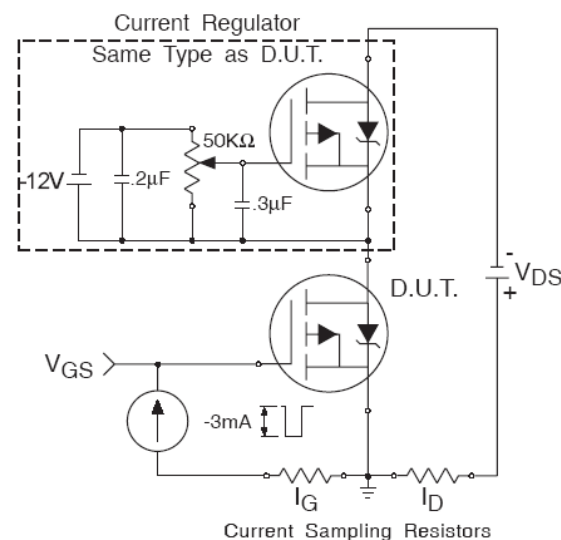


Fig 13b. Gate Charge Test Circuit

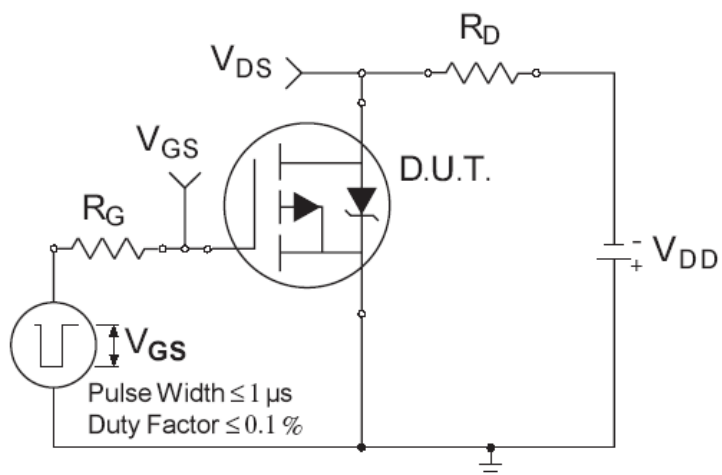


Fig 14a. Switching Time Test Circuit

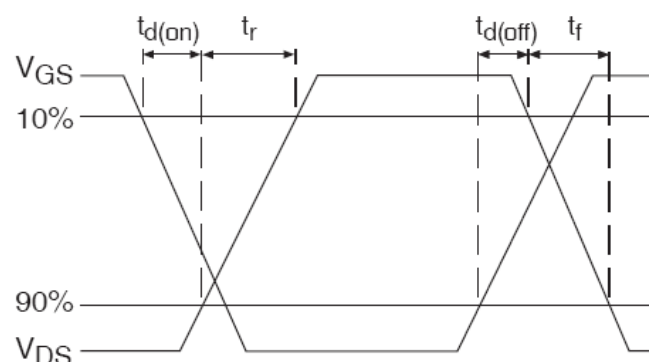
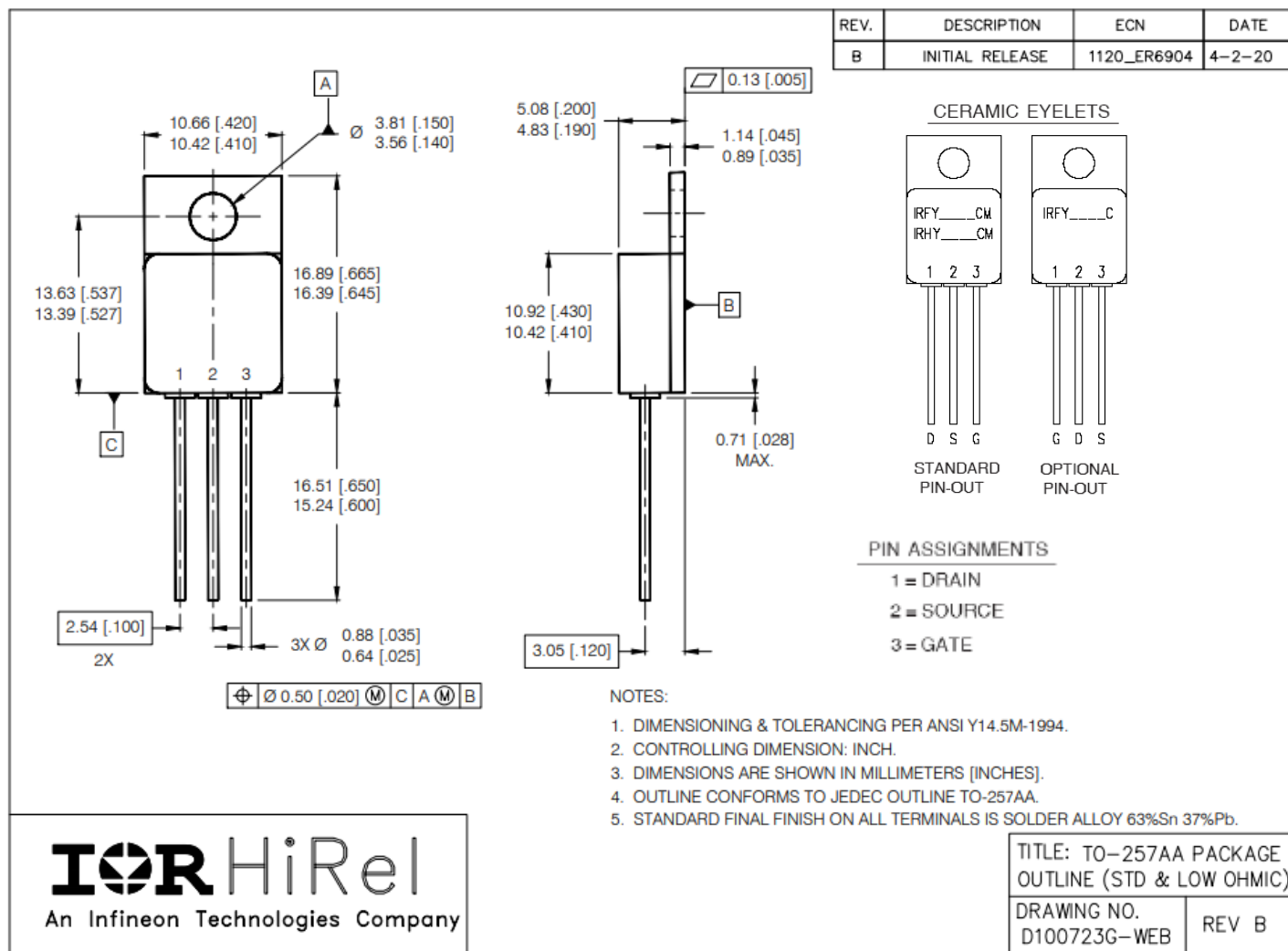


Fig 14b. Switching Time Waveforms

Note: For the most updated package outline, please see the website: [TO-257AA](http://www.infineon.com/to-257aa)

Case Outline and Dimensions - TO-257AA



BERYLLIA WARNING PER MIL-PRF-19500

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

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